

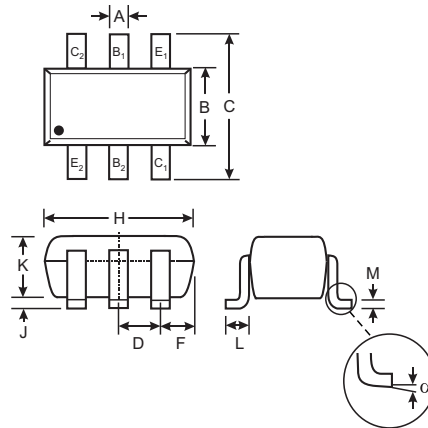
COMPLEMENTARY NPN / PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

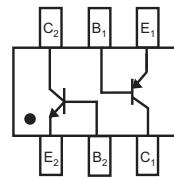
Complementary Pair
 Epitaxial Planar Die Construction
 One 2222A Type (NPN),
 One 2907A Type (PNP)
 Ideal for Low Power Amplification and Switching
Lead Free By Design/RoHS Compliant (Note 2)
"Green Device" (Note 3)

Mechanical Data

Case: SOT-26
 Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
 Moisture Sensitivity: Level 1 per J-STD-020C
 Terminals: Finish - Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
 Terminal Connections: See Diagram
 Ordering & Date Code Information: See Page 3
 Marking (See Page 3): K27
 Weight: 0.006 grams (approximate)



Note: E1, B1, and C1 = 2907A Type (PNP),
 E2, B2, and C2 = 2222A Type (NPN).
 Type marking indicates orientation.



SOT-26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D			0.95
F			0.55
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
	0	8	
All Dimensions in mm			

Maximum Ratings, 2222A Type (NPN)

@ T_A = 25 °C unless otherwise specified

Characteristic	Symbol	2222A (NPN)	Unit
Collector-Base Voltage	V _{CBO}	75	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous	I _C	600	mA

Maximum Ratings, 2907A Type (PNP) @ T_A = 25 °C unless otherwise specified

Characteristic	Symbol	2907A (PNP)	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous	I _C	-600	mA

Maximum Ratings, Total @ T_A = 25 °C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P _d	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{JA}	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Note:
- Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 - No purposefully added lead.
 - Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Electrical Characteristics, 2222A Type (NPN)

 @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	75		V	$I_C = 10\text{ A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40		V	$I_C = 10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0		V	$I_E = 10\text{ A}, I_C = 0$
Collector Cutoff Current	I_{CBO}		10	nA A	$V_{CB} = 60\text{V}, I_E = 0$ $V_{CB} = 60\text{V}, I_E = 0, T_A = 150^\circ\text{C}$
Collector Cutoff Current	I_{CEX}		10	nA	$V_{CE} = 60\text{V}, V_{EB(OFF)} = 3.0\text{V}$
Emitter Cutoff Current	I_{EBO}		10	nA	$V_{EB} = 3.0\text{V}, I_C = 0$
Base Cutoff Current	I_{BL}		20	nA	$V_{CE} = 60\text{V}, V_{EB(OFF)} = 3.0\text{V}$
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h_{FE}	35 50 75 100 40 50 35	300		$I_C = 100\text{ A}, V_{CE} = 10\text{V}$ $I_C = 1.0\text{mA}, V_{CE} = 10\text{V}$ $I_C = 10\text{mA}, V_{CE} = 10\text{V}$ $I_C = 150\text{mA}, V_{CE} = 10\text{V}$ $I_C = 500\text{mA}, V_{CE} = 10\text{V}$ $I_C = 10\text{mA}, V_{CE} = 10\text{V}, T_A = -55^\circ\text{C}$ $I_C = 150\text{mA}, V_{CE} = 1.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$		0.3 1.0	V	$I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.6	1.2 2.0	V	$I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}		8	pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{ibo}	—	25	pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Current Gain-Bandwidth Product	f_T	300		MHz	$V_{CE} = 20\text{V}, I_C = 20\text{mA}, f = 100\text{MHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_d		10	ns	$V_{CC} = 30\text{V}, I_C = 150\text{mA}, V_{BE(off)} = -0.5\text{V}, I_{B1} = 15\text{mA}$
Rise Time	t_r		25	ns	
Storage Time	t_s		225	ns	$V_{CC} = 30\text{V}, I_C = 150\text{mA}, I_{B1} = I_{B2} = 15\text{mA}$
Fall Time	t_f		60	ns	

 Note: 4. Pulse test: Pulse width 300 μs , duty cycle 2%.

Electrical Characteristics, 2907A Type (PNP) @ $T_A = 25^\circ\text{C}$ unless otherwise specified

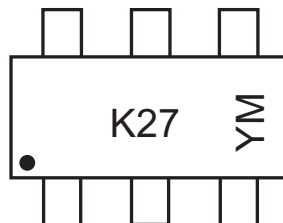
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60		V	$I_C = -10\text{ A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60		V	$I_C = -10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0		V	$I_E = -10\text{ A}, I_C = 0$
Collector Cutoff Current	I_{CBO}		-10	nA A	$V_{CB} = -50\text{V}, I_E = 0$ $V_{CB} = -50\text{V}, I_E = 0, T_A = 125^\circ\text{C}$
Collector Cutoff Current	I_{CEX}		-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -0.5\text{V}$
Base Cutoff Current	I_{BL}		-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -0.5\text{V}$
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h_{FE}	75 100 100 100 50	300		$I_C = -100\mu\text{A}, V_{CE} = -10\text{V}$ $I_C = -1.0\text{mA}, V_{CE} = -10\text{V}$ $I_C = -10\text{mA}, V_{CE} = -10\text{V}$ $I_C = -150\text{mA}, V_{CE} = -10\text{V}$ $I_C = -500\text{mA}, V_{CE} = -10\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$		-0.4 -1.6	V	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$		-1.3 -2.6	V	$I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}		8.0	pF	$V_{CB} = -10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{ibo}	—	30	pF	$V_{EB} = -2.0\text{V}, f = 1.0\text{MHz}, I_C = 0$
Current Gain-Bandwidth Product	f_T	200		MHz	$V_{CE} = -20\text{V}, I_C = -50\text{mA}, f = 100\text{MHz}$
SWITCHING CHARACTERISTICS					
Turn-On Time	t_{on}		45	ns	$V_{CC} = -30\text{V}, I_C = -150\text{mA}, I_{B1} = -15\text{mA}$
Delay Time	t_d		10	ns	
Rise Time	t_r		40	ns	
Turn-Off Time	t_{off}		100	ns	$V_{CC} = -6.0\text{V}, I_C = -150\text{mA}, I_{B1} = I_{B2} = -15\text{mA}$
Storage Time	t_s		80	ns	
Fall Time	t_f		30	ns	

Note: 5. Short duration pulse test used to minimize self-heating effect.

Ordering Information (Note 6)

Device	Packaging	Shipping
MMDT2227M-7	SOT-26	3000/Tape & Reel

Note: 6. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information


K27 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: S = 2005
 M = Month ex: 9 = September

Date Code Key

Year	2005	2006	2007	2008	2009	2010	2011	2012
Code	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

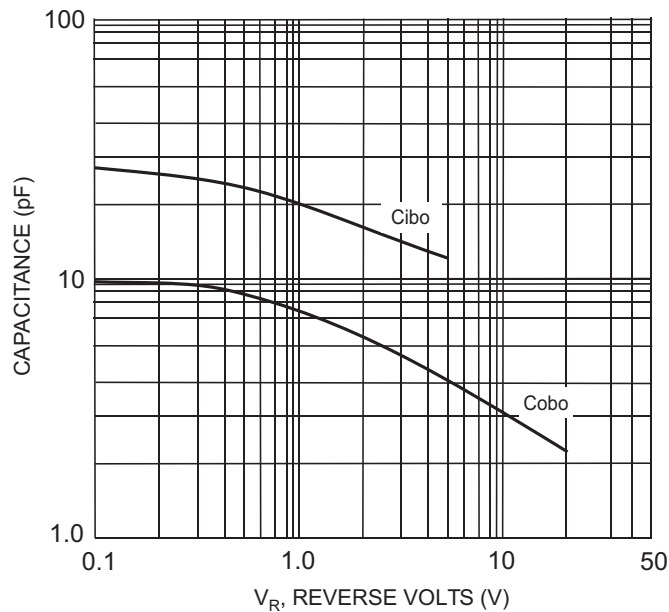


Fig. 1 (2222A) Typical Capacitance

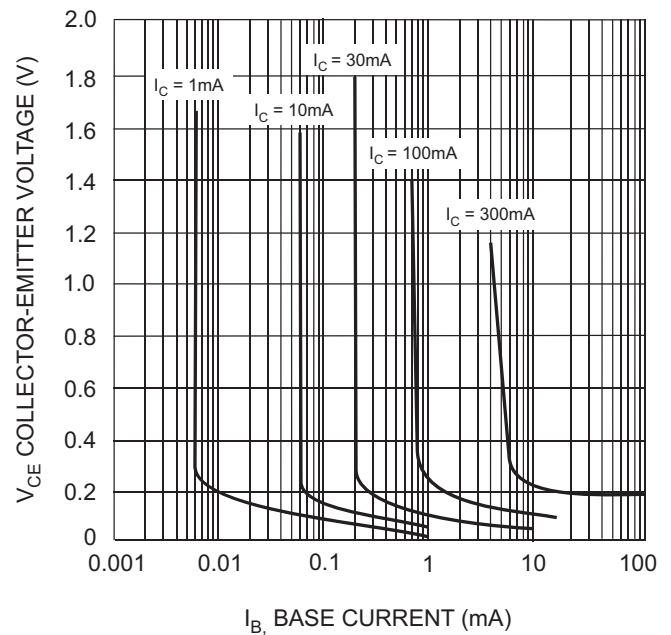


Fig. 2 (2222A) Typical Collector Saturation Region

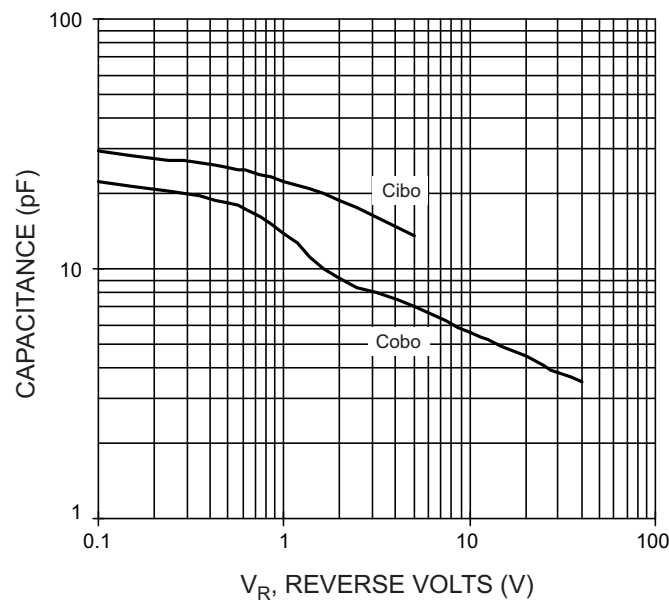


Fig. 3 (2907A) Typical Capacitance

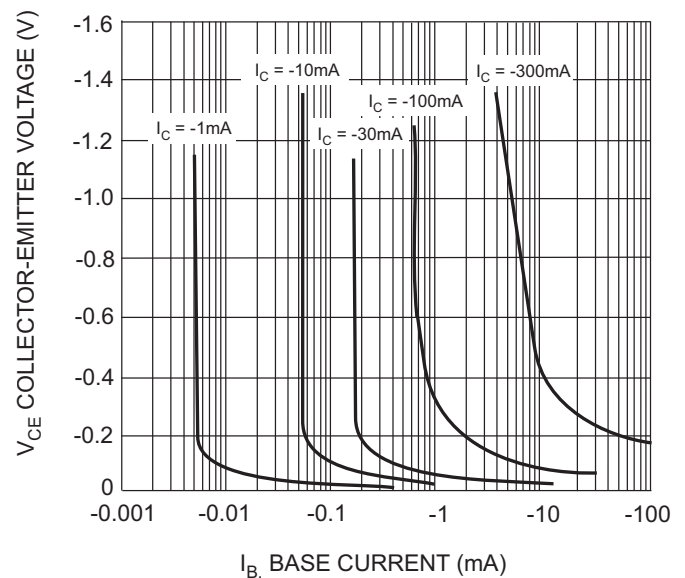


Fig. 4 (2907A) Typical Collector Saturation Region

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9